

Docket No.: MUH-12041

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By: [Signature]

Date: October 4, 2002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Heinz Hönigschmid
Applic. No. : 09/997,983
Filed : November 29, 2001
Title : Integrated Magnetoresistive Semiconductor Memory and
Fabrication Method for the Memory
Art Unit : 2185

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,
Washington, D.C. 20231

Sir:

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Technology Center 2100

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

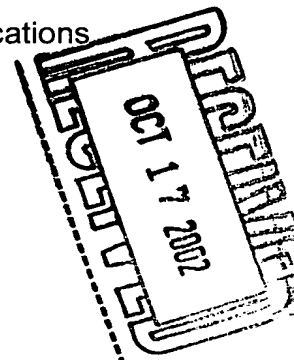
United States Patent No. 5,940,319 (Durlam et al.), dated August 17, 1999;

United States Patent No. 6,097,625 (Scheuerlein), dated August 1, 2000;

M. Durlam et al.: "Nonvolatile RAM based on Magnetic Tunnel Junction Elements",
2000 IEEE International Solid-State Circuits Conference, Digest of Technical Papers,
pp. 130-131;

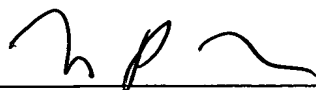
S. Tehrani et al.: "Recent Developments in Magnetic Tunnel Junction MRAM", *IEEE Transactions on Magnetics*, Vol. 36, No. 5, September 2000, pp. 2752-2757;

German Examination Report dated November 14, 2001.



If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,



For Applicant

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Date: October 4, 2002

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